

Amendments to the claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original) A method of forming a ferroelectric substance thin film comprising:
forming a seed layer including ultra-fine particle powder containing an element constituting a ferroelectric substance thin film on a surface of a substrate; and
forming the ferroelectric substance thin film on the seed layer.
2. (original) The method of forming a ferroelectric substance thin film as claimed in claim 1, wherein forming the seed layer includes:
applying solution containing an element constituting the ferroelectric substance thin film to the surface of the substrate; and
drying and baking the solution applied to the substrate.
3. (original) The method of forming a ferroelectric substance thin film according to claim 2, wherein forming the ferroelectric substance thin film includes annealing the seed layer for crystallization.
- 4-5. (cancelled)
6. (original) A method of forming a ferroelectric substance memory including an FET of an MFMIS structure, said method comprising:
forming a gate insulating film on a semiconductor substrate and between source-drain regions;
forming a floating gate on the gate insulating film;
forming a ferroelectric substance layer on the floating gate; and
forming a control gate on the ferroelectric substance layer,
wherein forming the ferroelectric substance layer comprises:
forming a seed layer including an ultra-fine particle powder containing an element constituting a ferroelectric substance thin film on a surface of the floating gate; and

forming the ferroelectric substance thin film on the seed layer.

7. (original) A method of forming a ferroelectric substance memory including an FET of an MFMIS structure, said method comprising:

forming a gate insulating film on the surface of the semiconductor substrate and between a source-drain regions;

forming a floating gate on the gate insulating film;

forming a ferroelectric substance layer on the floating gate; and

forming a control gate on the ferroelectric substance layer,

wherein forming the ferroelectric substance layer comprises:

applying a ferroelectric substance thin film applying liquid including ultra-fine particle powder containing at least one kind of elements constituting a ferroelectric substance thin film to a surface of the floating gate; and

baking the ferroelectric substance thin film applying liquid applied to the surface of the floating gate.

8. (original) A method of forming a ferroelectric substance memory comprising:

forming an FET including a gate electrode formed on a surface of a semiconductor substrate between source-drain regions formed on surface of the semiconductor substrate through a gate insulating film; and

forming a ferroelectric substance capacitor connected with one of the source-drain regions of the FET through a storage node contact,

wherein forming the ferroelectric substance capacitor comprises:

forming a first electrode; a process

applying ferroelectric substance thin film applying liquid including ultra-fine particle powder containing at least one kind of elements constituting the ferroelectric substance thin film to the surface of the first electrode;

form a ferroelectric substance thin film by baking ferroelectric substance thin film applying liquid applied to the surface of the first electrode; and

forming a second electrode on the ferroelectric substance thin film.

9. (original) A method of forming a ferroelectric substance memory comprising:

- forming an FET including a gate electrode formed on a surface of a semiconductor substrate between source-drain regions formed on a surface of the semiconductor substrate through a gate insulating film; and
- forming a ferroelectric substance capacitor connect with one of the source-drain regions of the FET through a storage node contact,

wherein forming the ferroelectric substance capacitor comprises:

- forming a first electrode;
- forming a seed layer including ultra-fine particle powder containing an element constituting a ferroelectric substance thin film on a surface of the first electrode; and
- forming the ferroelectric substance thin film on the seed layer.